

JUNCTION FIELD EFFECT TRANSISTOR 2SK660

N-CHANNEL SILICON JUNCTION FIELD EFFECT TRANSISTOR FOR IMPEDANCE CONVERTER OF ECM

DESCRIPTION

The 2SK660 is suitable for converter of ECM.

FEATURES

- · Compact package
- High forward transfer admittance
 Was 1 = 1200 us TVR (Vrs = 5 V ls = 0 us
- | yfs | = 1200 μ S TYP. (VDS = 5 V, ID = 0 μ A)
- Low capacitance

Ciss = 4.5 pF (VDS = 5 V, VGS = 0 V, f = 1 MHz)

• Includes diode and high resistance at G - S

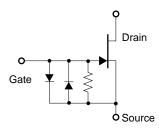
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK660	SST

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage Note	VDSX	20	V	
Gate to Drain Voltage	Vgdo	-20	V	
Drain Current	lσ	10	mΑ	
Gate Current	lg	10	mΑ	
Total Power Dissipation	PT	100	mW	
Junction Temperature	Tj	125	°C	
Storage Temperature	T _{stg}	-55 to +125	°C	

EQUIVALENT CIRCUIT



Note $V_{GS} = -1.0 \text{ V}$

Remark Please take care of ESD (Electro Static Discharge) when you handle the device in this document.

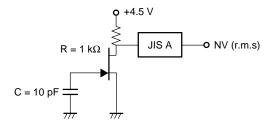
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ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Cut-off Current	Ipss	VDS = 5.0 V, VGS = 0 V	60		500	μΑ
Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = 5.0 \text{V}, I_{D} = 1.0 \mu \text{A}$			-1.0	٧
Forward Transfer Admittance	y fs1	$V_{DS} = 5.0 \text{V}, \text{Id} = 30 \mu\text{A}, \text{f} = 1.0 \text{kHz}$	150			μS
Forward Transfer Admittance	y fs2	V _{DS} = 5.0 V, V _{GS} = 0 V, f = 1.0 kHz	150	1200		μS
Input Capacitance	Ciss	Vps = 5.0 V		4.5	6.0	pF
Output Capacitance	Coss	Ves = 0 V		1.5	3.0	pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		1.2	3.0	pF
Noise Voltage	NV	See Test Circuit		1.0	3.0	μV

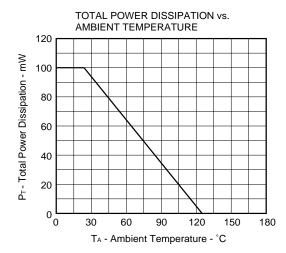
NOISE VOLTAGE TEST CIRCUIT

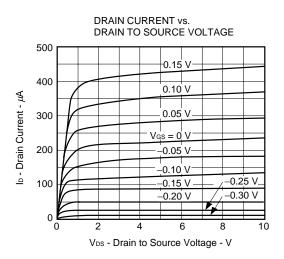


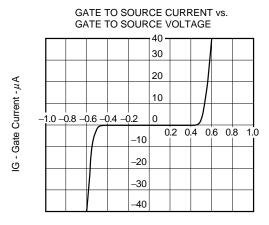
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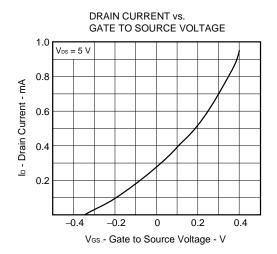


TYPICAL CHARACTERISTICS (TA = 25°C)

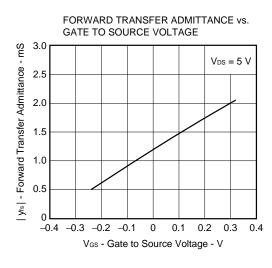


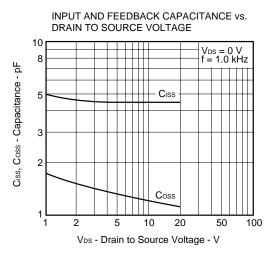






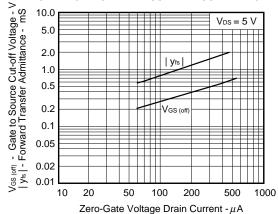
V_{GS} - Gate to Source Voltage - V



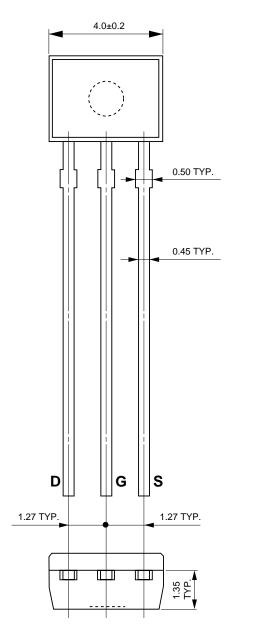


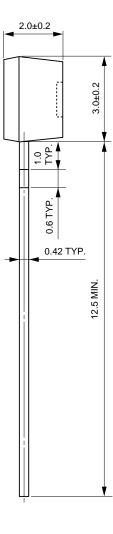
Data Sheet D10753EJ2V0DS 3

FORWARD TRANSFER ADMITTANCE AND GATE TO SOURCE CUT-OFF VOLTAGE vs. ZERO-GATE VOLTAGE DRAIN CURRENT CO-RELATION



PACKAGE DRAWING (Unit: mm)





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[MEMO]

[MEMO]

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